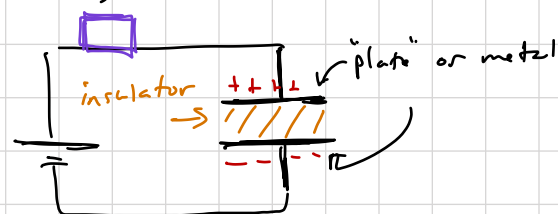


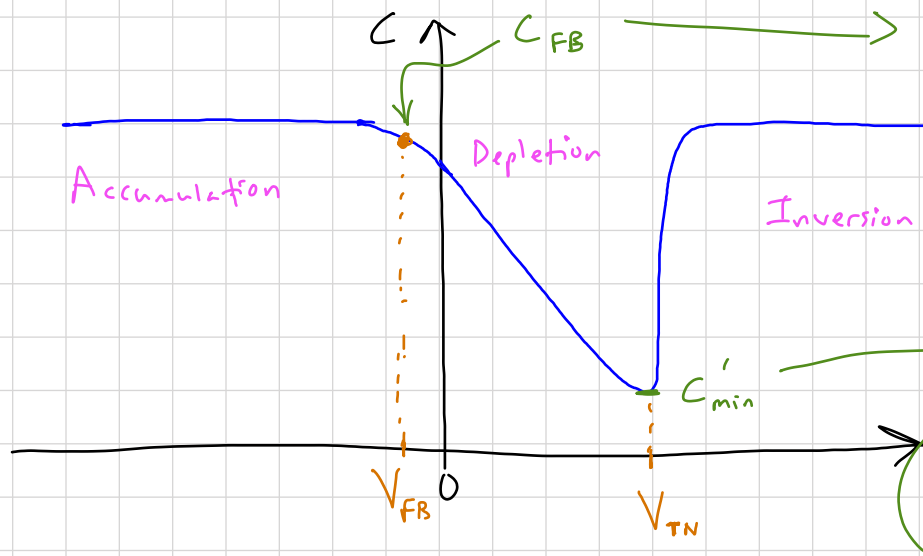
Capacitance is an AC parameter, not DC, thus is measured by adding a small-signal AC onto an applied DC signal.

$$C = \frac{dQ}{dV} \sim \text{change in charge} / \text{change in voltage}$$



Ideal C-V

- No oxide trapped charges and no interface states (at oxide-Si interface)
- Low-frequency AC signal (example using p-type mos-c)



Flat Band Capacitance:

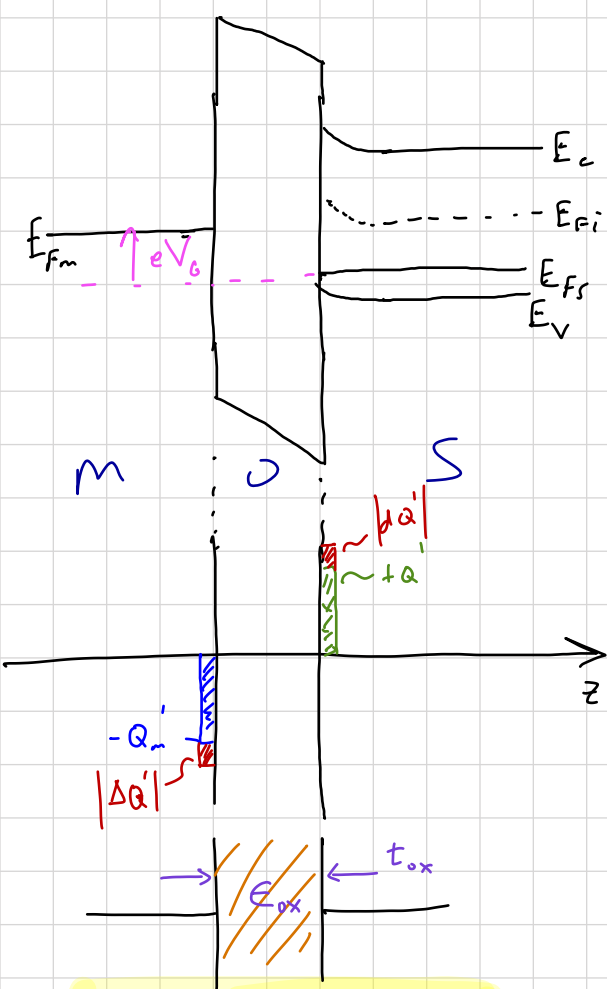
$$C'_{FB} = \frac{\epsilon_{ox} \epsilon_0}{t_{ox} + \left(\frac{\epsilon_{ox}}{\epsilon_s} \right) \sqrt{V_t \left(\frac{\epsilon_s \epsilon_0}{e N_a} \right)}}$$

when $x_d = x_{dT}$ ($V_G = V_T$):

$$C'_{min} = \frac{\epsilon_{ox} \epsilon_0}{t_{ox} + \left(\frac{\epsilon_{ox}}{\epsilon_s} \right) x_{dT}}$$

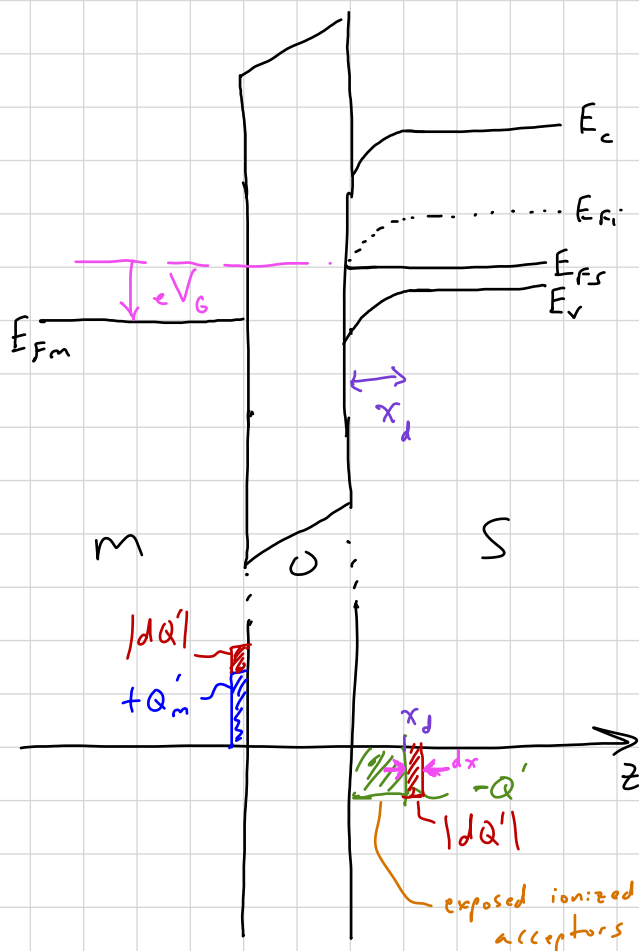
V_G → DC voltage

Accumulation



$$C'_{(acc)} = C_{ox} = \frac{\epsilon_{ox} \epsilon_0}{t_{ox}}$$

Depletion

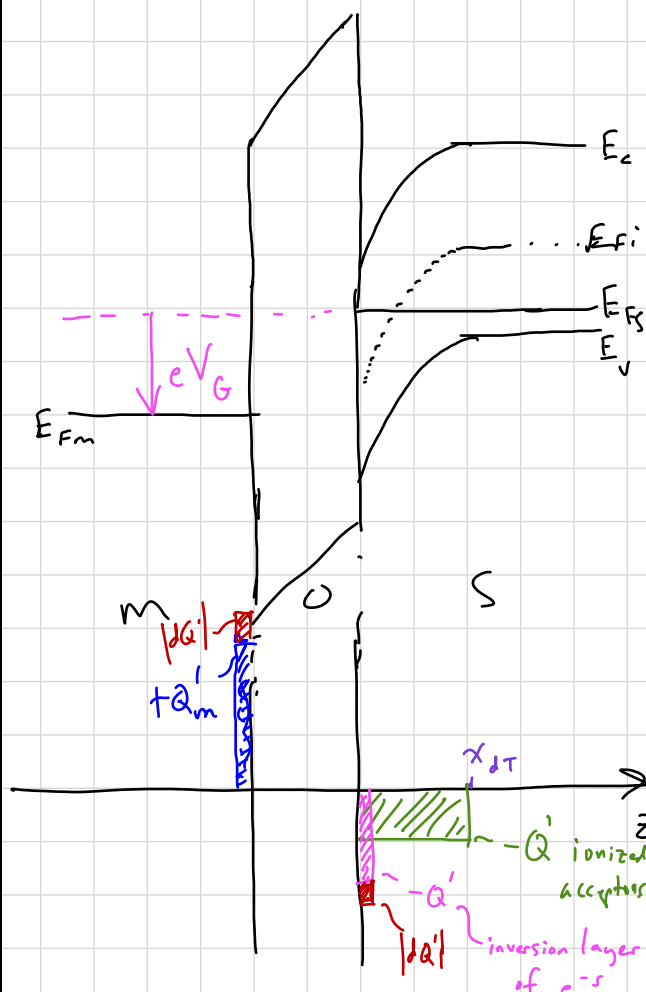


→ Because x_d will vary with dV_G , there is an additional capacitance: C_{SD}

$$\Rightarrow C'_{SD} = \frac{\epsilon_s \epsilon_0}{x_d}$$

$$C'_{(dpl)} = \frac{C'_{ox} C'_{SD}}{C'_{ox} + C'_{SD}} = \frac{\epsilon_{ox} \epsilon_0}{t_{ox} + \left(\frac{\epsilon_{ox}}{\epsilon_s} \right) x_d}$$

Inversion

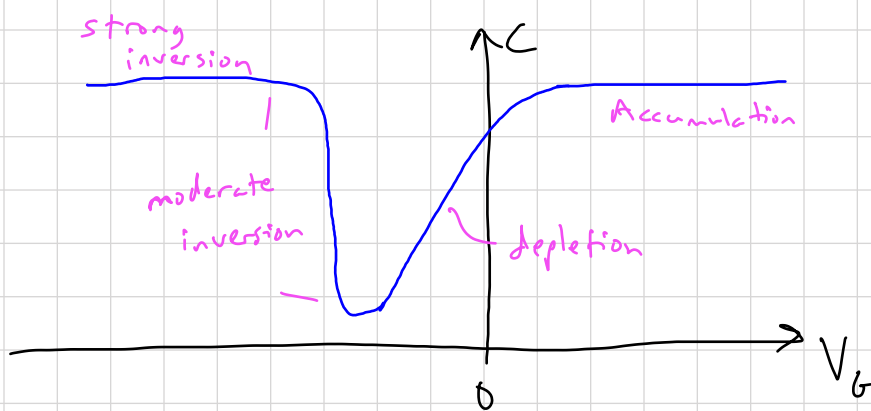


→ At low freq., the minority carriers are able to respond to dV_G by increase/decrease in inversion layer:

$$C'_{(inv)} = C_{ox} = \frac{\epsilon_{ox} \epsilon_0}{t_{ox}}$$

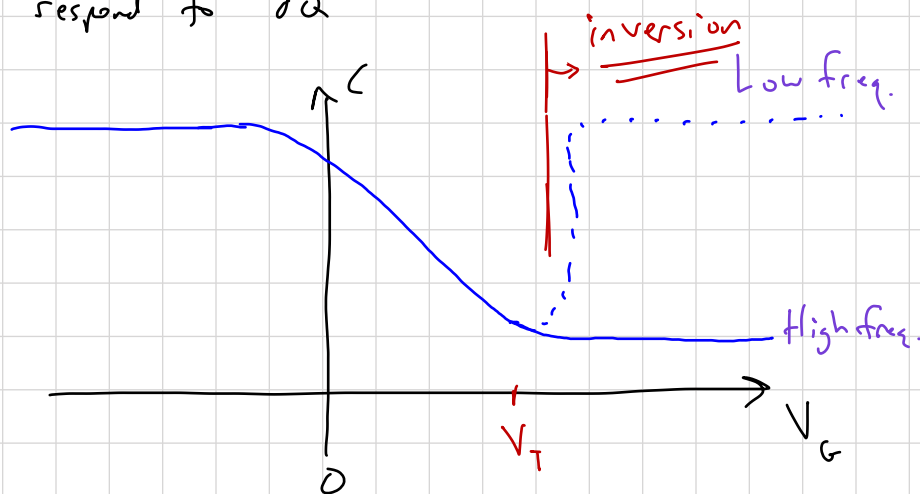
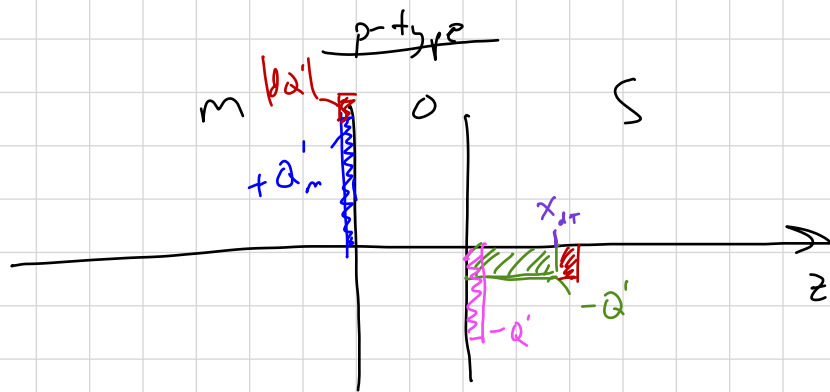
* at low frequency (~5-100 Hz)

What about n-type, ideal MOS?



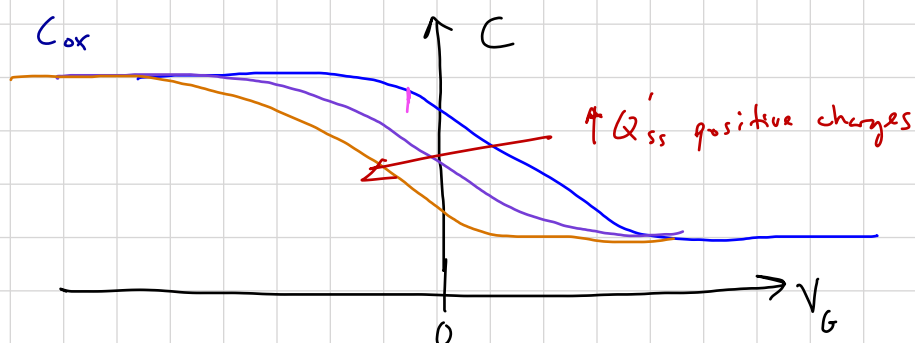
Frequency Effects

→ operation at high freq ($> 1 \text{ MHz}$) does not allow sufficient time for minority carrier diffusion, hence x_d goes beyond x_{dT} to respond to dQ'



Fixed/Trapped oxide charges

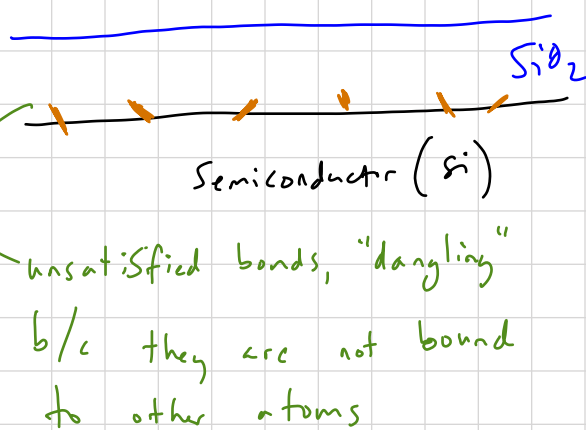
Consider: $V_{FB} = \phi_{ms} - \frac{Q_{ss}'}{C_{ox}}$ → V_{FB} will shift more negative with positive fixed charge and vice versa



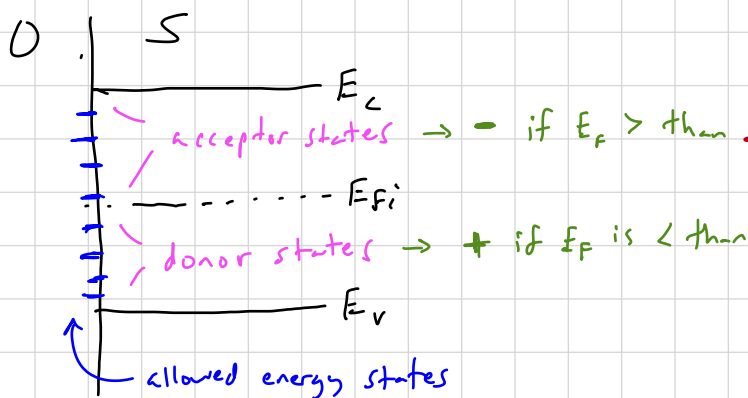
Interface traps/states at oxide-S.C.

→ much trickier than fixed charge because they will fill and empty of charge either + or - depending on bias conditions and even sweep direction:

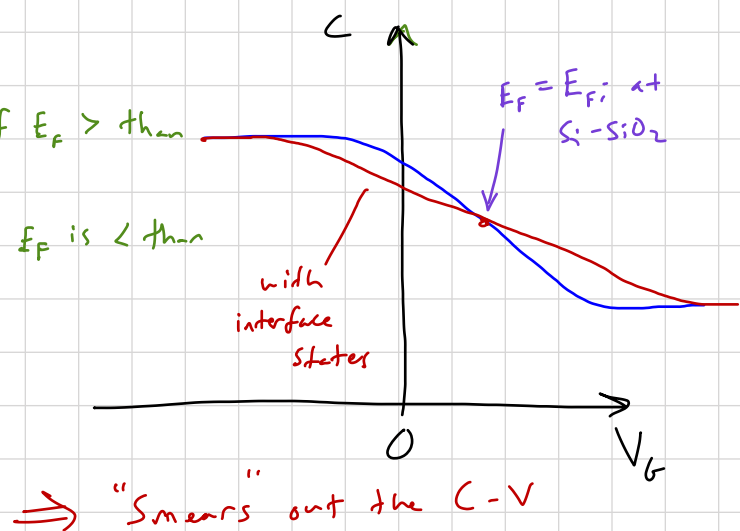
Physically:



Energy Space:



C-V:



⇒ "Smears" out the C-V